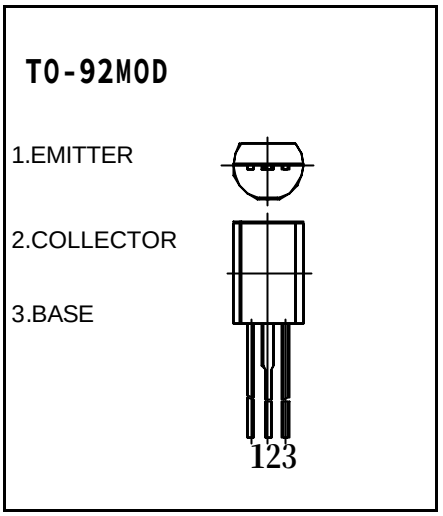
TO-92MOD Plastic-Encapsulate Transistors

AV966 TRANSISTOR (PNP)



FEATURE

Power dissipation

P_{CM} : 0.9 W (Tamb=25℃)

Collector current

I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= -1mA , I_E=0	-30		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-30		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -1mA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0		-0.1	μA
DC current gain	$h_{FE\ (1)}$	V_{CE}=-2 V, I_C= -500mA	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1.5 A, I_B= -0.03A		-2	V
Base-emitter voltage	V_{BE}	I_C= -500 mA, V_{CE}= -2V		-1	V
Transition frequency	f_T	V_{CE}= -2 V, I_C= -500mA	100		MHz

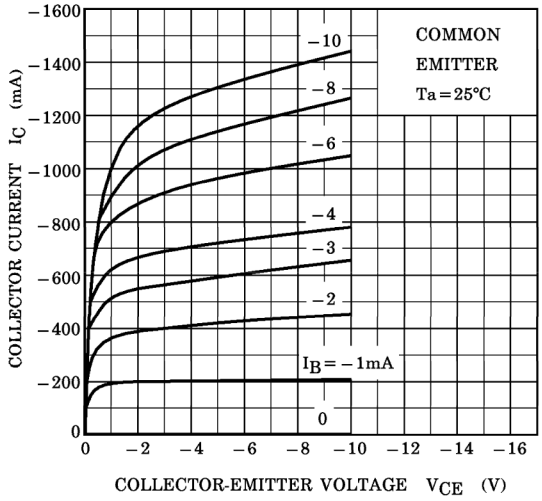
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320

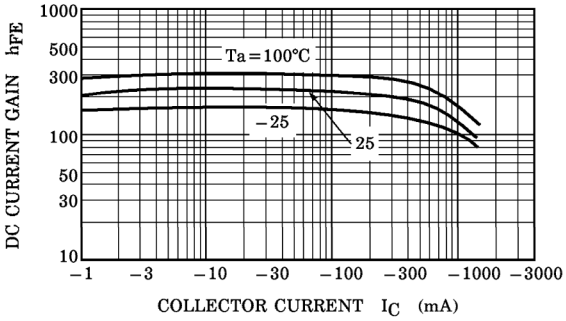
Copyright @vic Electronics Corp.

Typical Characteristics

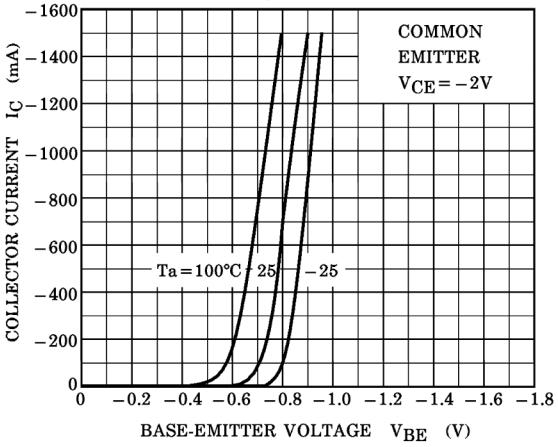
I_C – V_{CE}



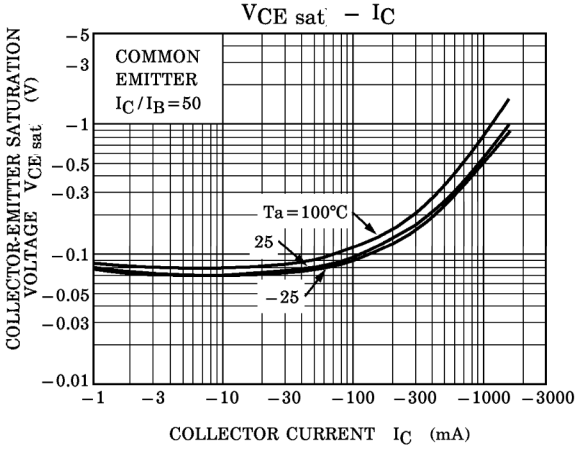
h_{FE} – I_C



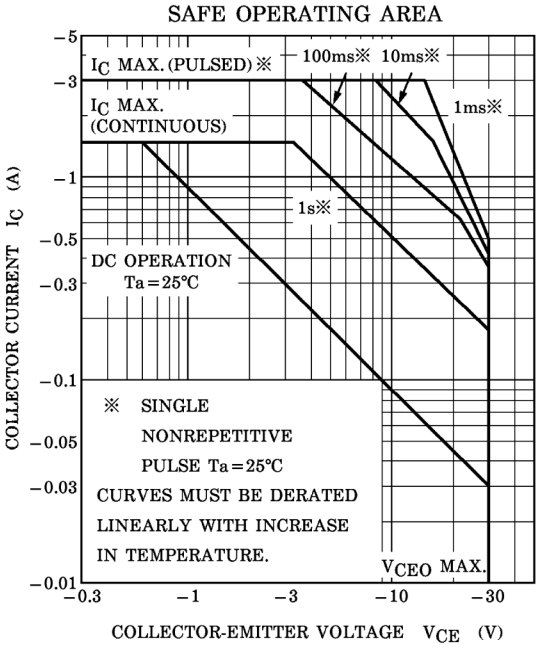
I_C – V_{BE}



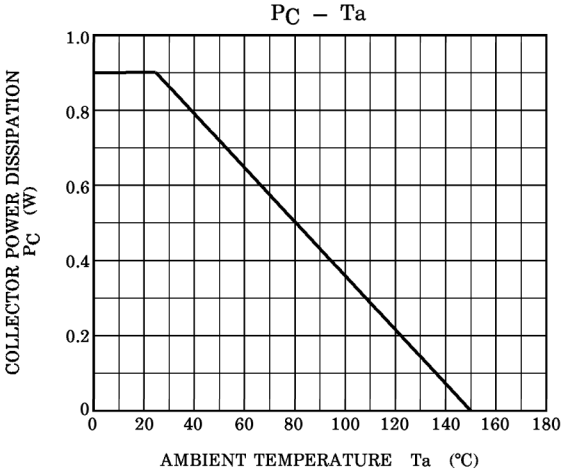
$V_{CE\ sat}$ – I_C



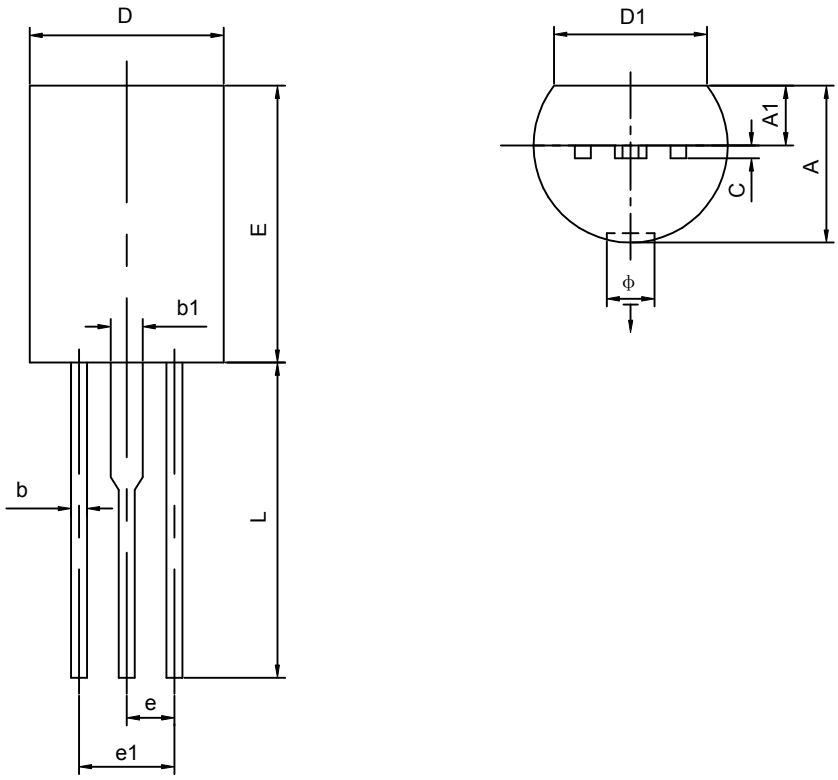
SAFE OPERATING AREA



P_C – Ta



TO-92MOD PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.700	5.100	0.185	0.201
A1	1.730	2.030	0.068	0.080
b	0.400	0.600	0.016	0.024
b1	0.900	1.100	0.035	0.043
c	0.400	0.500	0.016	0.020
D	5.800	6.200	0.228	0.244
D1	4.000		0.157	
E	8.400	8.800	0.331	0.346
e	1.500TYP		0.059TYP	
e1	2.900	3.100	0.114	0.122
L	13.050	13.450	0.514	0.530
Ö		1.600		0.063
⊤	0.000	0.380	0.000	0.015